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<u>Diodes Incorporated</u> <u>DMP2160UFDB-7</u>

For any questions, you can email us directly: sales@integrated-circuit.com

Datasheet of DMP2160UFDB-7 - MOSFET 2P-CH 20V 3.8A 6UDFN

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DMP2160UFDB

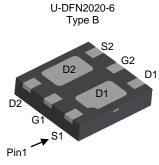
DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Features

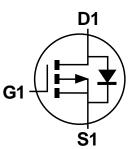
- Low On-Resistance
 - $70m\Omega @V_{GS} = -4.5V$
 - $85m\Omega @V_{GS} = -2.5V$
 - 86mΩ (typ) @V_{GS} = -1.8V
- Low Gate Threshold Voltage, -0.9V Max
- Fast Switching Speed
- Low Input/Output Leakage
- Low Profile, 0.5mm Max Height
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

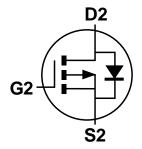
Mechanical Data

- Case: U-DFN2020-6 Type B
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 ⁶⁴
- Weight: 0.0065 grams (Approximate)









Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2160UFDB-7	U-DFN2020-6 Type B	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-DFN2020-6 Type B



P2 = Marking Code YM = Date Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September) Dot Denotes Pin 1

Date Code Key

Year	2008	2009		2015	201	6 20	17	2018	2019	2020	2021	2022
Code	V	W		С	D		Е	F	G	Н	I	J
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	y Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

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DMP2160UFDB

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±12	V
Drain Current (Note 5)	I _D	-3.8	А
Pulsed Drain Current (Note 6)	I _{DM}	-13	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_{D}	1.4	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	89	°C/W
Operating and Storage Temperature Range	TJ, T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7							
Drain-Source Breakdown Voltage	BV _{DSS}	-20		_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
Gate-Source Leakage	I _{GSS}	_		±800		$V_{GS} = \pm 12V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(th)}$	-0.45	_	-0.9	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
		_	54	70		$V_{GS} = -4.5V, I_D = -2.8A$	
Static Drain-Source On-Resistance	R _{DS (ON)}	_	68	85		$V_{GS} = -2.5V, I_D = -2.0A$	
		_	86	_		$V_{GS} = -1.8V, I_{D} = -1.0A$	
Forward Transfer Admittance	Y _{fs}	_	8	_	S	$V_{DS} = -5V, I_{D} = -2.8A$	
Diode Forward Voltage (Note 7)	V _{SD}	_	0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1.6A$	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{iss}		536	_	pF	V 40V V 0V	
Output Capacitance	Coss	_	68	—	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss		59	_	рF	1 – 1.0101112	
Gate Resistance	R_g	ı	34	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Q_{g}	-	6.5	-	nC	\\\\ 4.5\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Gate-Source Charge	Q_{gs}	ı	8.0	-	nC	$V_{GS} = -4.5V, V_{DD} = -10V,$ $I_{D} = -1.5A$	
Gate-Drain Charge	Q_{gd}	-	1.4	-	nC	ID = -1.5A	
Turn-On Delay Time	t _{D(on)}	ı	11.51	-	ns		
Turn-On Rise Time	t _r	ı	12.09	-	ns	$V_{GEN} = -4.5V, V_{DD} = -10V,$	
Turn-Off Delay Time	t _{D(off)}	-	55.34	-	ns	$R_L = 10\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _f	1	27.54	-	ns		

Notes:

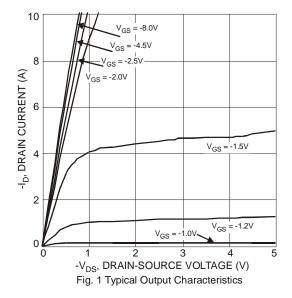
- Device mounted on FR-4 PCB, on minimum recommended, 2oz Copper pad layout. Repetitive rating, pulse width limited by junction temperature. Short duration pulse test used to minimize self-heating effect.

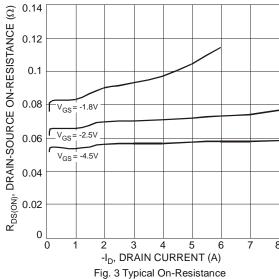
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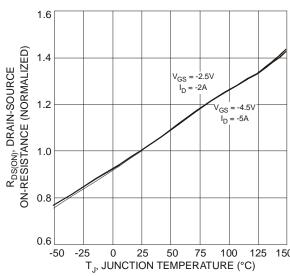
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vs. Drain Current and Gate Voltage

Fig. 5 On-Resistance Variation with Temperature

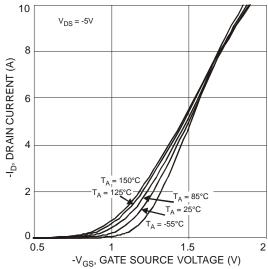


Fig. 2 Typical Transfer Characteristics

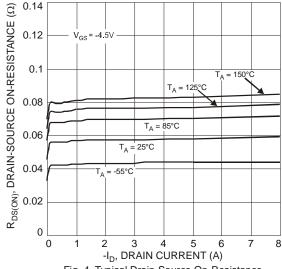


Fig. 4 Typical Drain-Source On-Resistance vs. Drain Current and Temperature

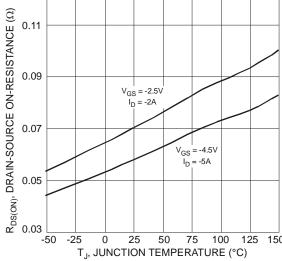


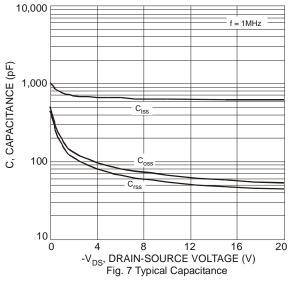
Fig. 6 On-Resistance Variation with Temperature

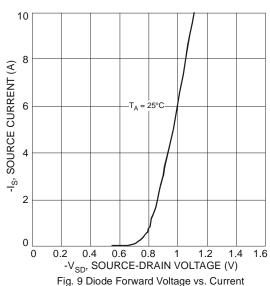
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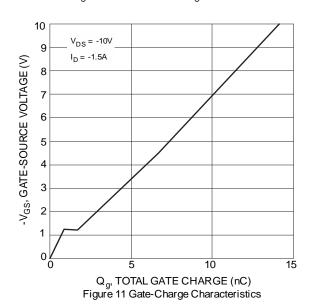
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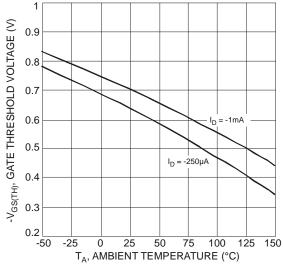


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

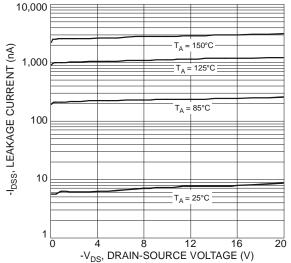


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage

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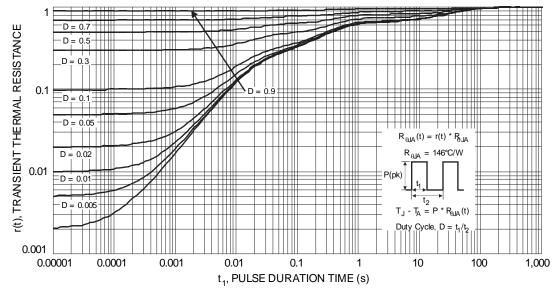
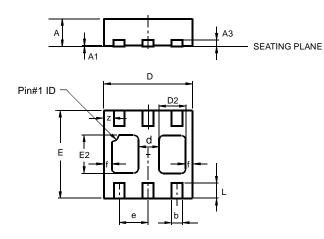


Fig. 12 Transient Thermal Response

Package Outline Dimensions

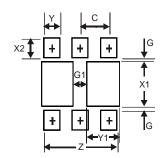
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



U-DFN2020-6							
Type B							
Dim	Min	Max	Тур				
Α	0.545	0.605	0.575				
A1	0	0.05	0.02				
A3	_	_	0.13				
b	0.20	0.30	0.25				
D	1.95	2.075	2.00				
d	_	_	0.45				
D2	0.50	0.70	0.60				
е	_	_	0.65				
E	1.95	2.075	2.00				
E2	0.90	1.10	1.00				
f	_	_	0.15				
L	0.25	0.35	0.30				
Z	_	_	0.225				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
С	0.65



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